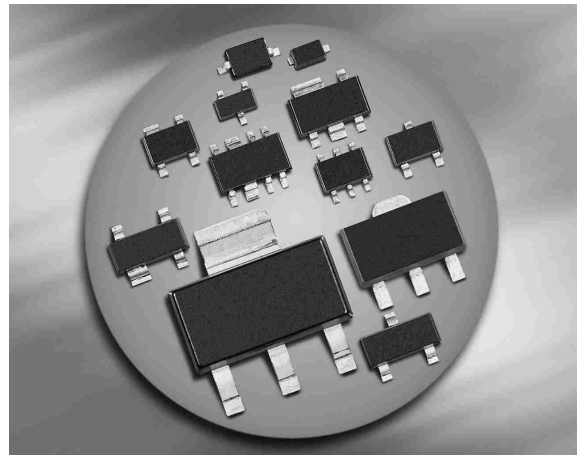
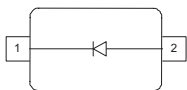


Silicon PIN Diode

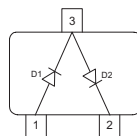
- High voltage current controlled RF resistor for RF attenuator and switches
- Frequency range above 1 MHz up to 6 GHz
- Very low capacitance at zero volt reverse bias at frequencies above 1 GHz (typ. 0.17 pF)
- Low forward resistance (typ. 2.1 Ω @ 10 mA)
- Very low signal distortion
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101¹⁾



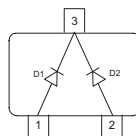
BAR64-02EL
BAR64-02V
BAR64-03W



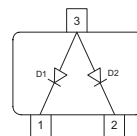
BAR64-04
BAR64-04W



BAR64-05
BAR64-05W



BAR64-06
BAR64-06W



Type	Package	Configuration	L_S (nH)	Marking
BAR64-02EL*	TSLP-2-19	single, leadless	0.4	OE
BAR64-02V	SC79	single	0.6	O
BAR64-03W	SOD323	single	1.8	blue 2
BAR64-04	SOT23	series	1.8	PPs
BAR64-04W	SOT323	series	1.4	PPs
BAR64-05	SOT23	common cathode	1.8	PRs
BAR64-05W	SOT323	common cathode	1.4	PRs
BAR64-06	SOT23	common anode	1.8	PSs
BAR64-06W	SOT323	common anode	1.4	PSs

¹⁾BAR64-02EL is not qualified according AEC Q101

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	150	V
Forward current	I_F	100	mA
Total power dissipation	P_{tot}		mW
BAR64-02EL, $T_S \leq 135^\circ\text{C}$		250	
BAR64-02V, $T_S \leq 125^\circ\text{C}$		250	
BAR64-03W, $T_S \leq 25^\circ\text{C}$		250	
BAR64-04, -05, -06, $T_S \leq 65^\circ\text{C}$		250	
BAR64-04W, -05W, -06W, $T_S \leq 115^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BAR64-02EL		≤ 60	
BAR64-02V, -04W, -05W, -06W		≤ 140	
BAR64-03W		≤ 370	
BAR64-04, -05, -06		≤ 340	

¹⁾For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage	$V_{(\text{BR})}$	150	-	-	V
$I_{(\text{BR})} = 5 \mu\text{A}$					
Forward voltage	V_F	-	-	1.1	
$I_F = 50 \text{ mA}$					

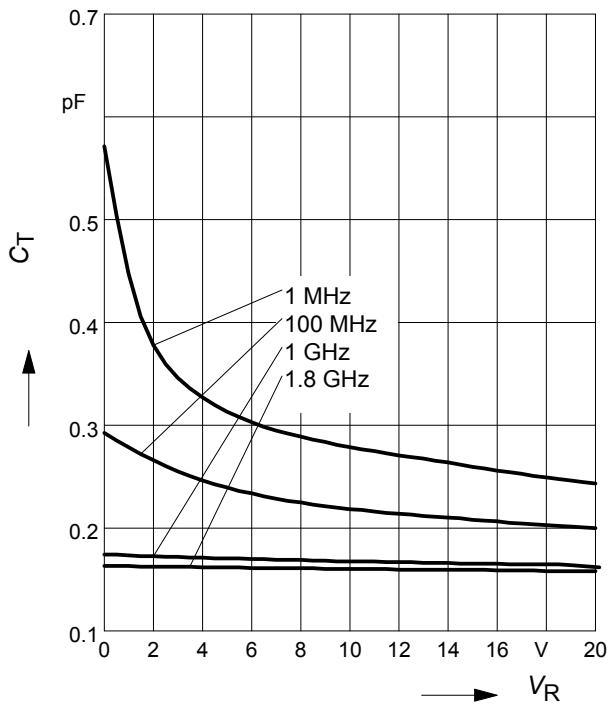
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 20\text{ V}$, $f = 1\text{ MHz}$ $V_R = 0\text{ V}$, $f = 100\text{ MHz}$ $V_R = 0\text{ V}$, $f = 1\ldots 1.8\text{ GHz}$, BAR64-02EL $V_R = 0\text{ V}$, $f = 1\ldots 1.8\text{ GHz}$, all other	C_T	- - - -	0.23 0.3 0.13 0.17	0.35 - - -	pF
Reverse parallel resistance $V_R = 0\text{ V}$, $f = 100\text{ MHz}$ $V_R = 0\text{ V}$, $f = 1\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$	R_P	- - -	10 4 3	- - -	kΩ
Forward resistance $I_F = 1\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$ $I_F = 100\text{ mA}$, $f = 100\text{ MHz}$	r_f	- - -	12.5 2.1 0.85	20 2.8 1.35	Ω
Charge carrier life time $I_F = 10\text{ mA}$, $I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$	τ_{rr}	-	1550	-	ns
I-region width	W_I	-	50	-	μm
Insertion loss ¹⁾ $I_F = 3\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 5\text{ mA}$, $f = 1.8\text{ GHz}$ $I_F = 10\text{ mA}$, $f = 1.8\text{ GHz}$	I_L	- - -	0.32 0.23 0.16	- - -	dB
Isolation ¹⁾ $V_R = 0\text{ V}$, $f = 0.9\text{ GHz}$ $V_R = 0\text{ V}$, $f = 1.8\text{ GHz}$ $V_R = 0\text{ V}$, $f = 2.45\text{ GHz}$ $V_R = 0\text{ V}$, $f = 5.6\text{ GHz}$	I_{SO}	- - - -	22 17 14.5 8.5	- - - -	

¹⁾BAR64-02EL in series configuration, $Z = 50\text{ }\Omega$

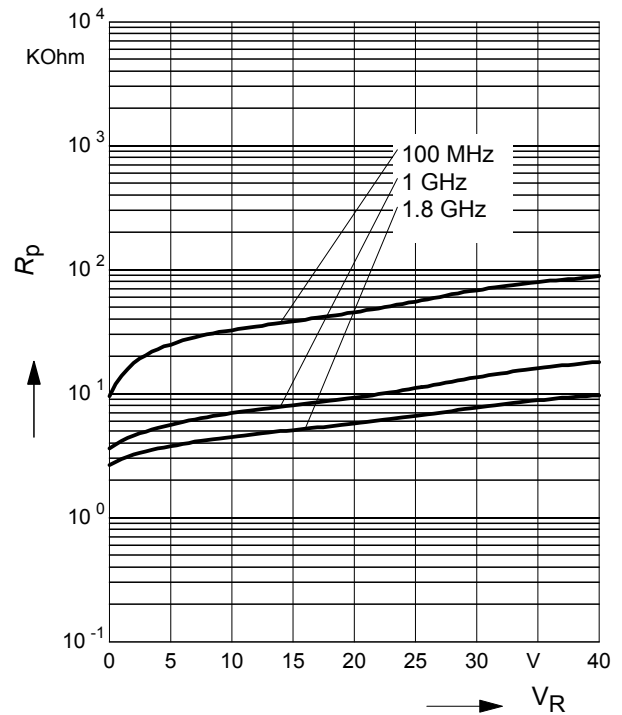
Diode capacitance $C_T = f(V_R)$

$f = \text{Parameter}$



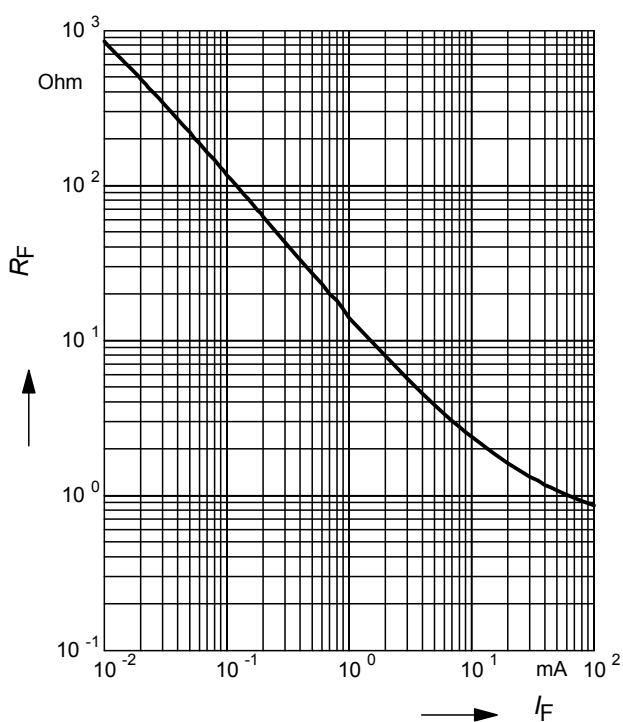
Reverse parallel resistance $R_P = f(V_R)$

$f = \text{Parameter}$



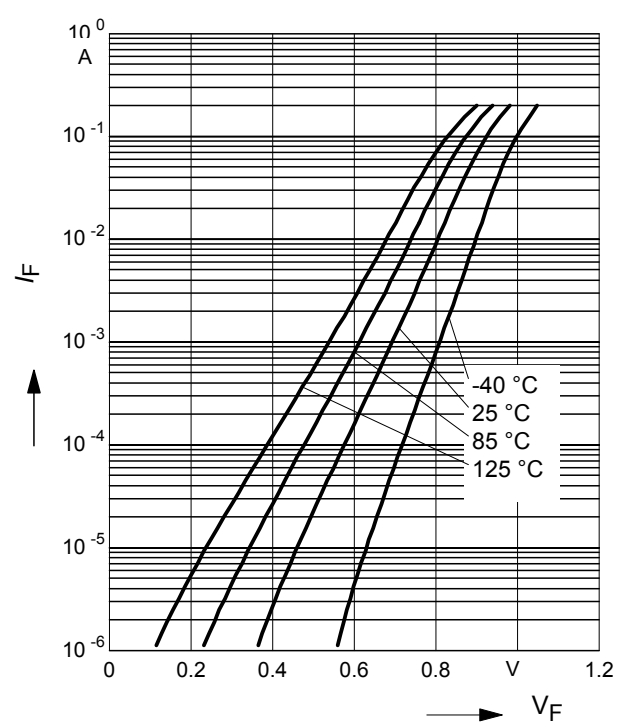
Forward resistance $r_f = f(I_F)$

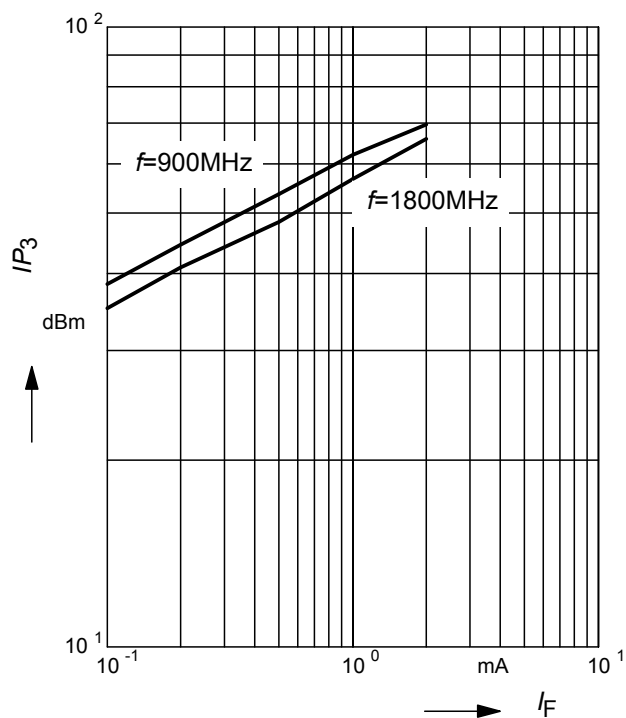
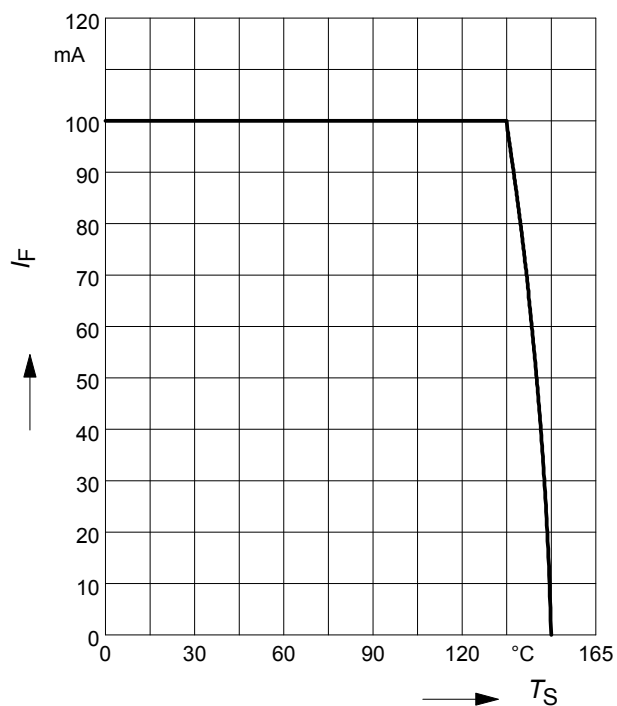
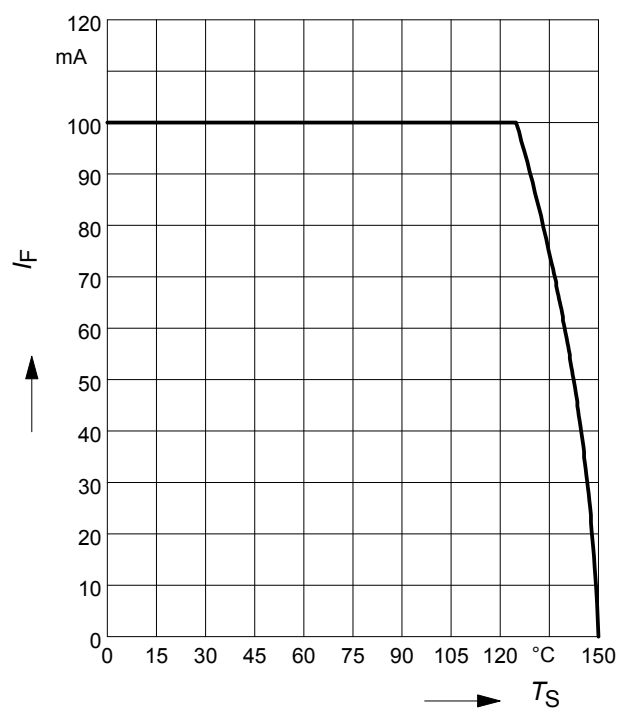
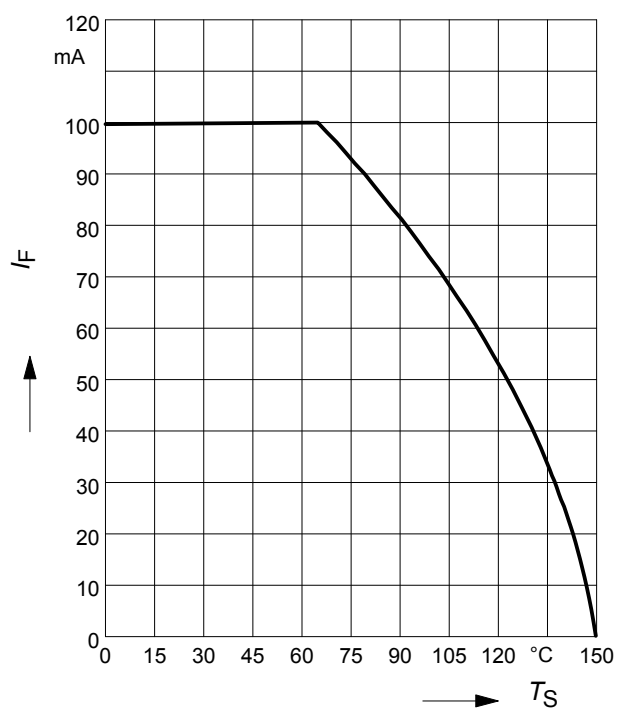
$f = 100\text{MHz}$



Forward current $I_F = f(V_F)$

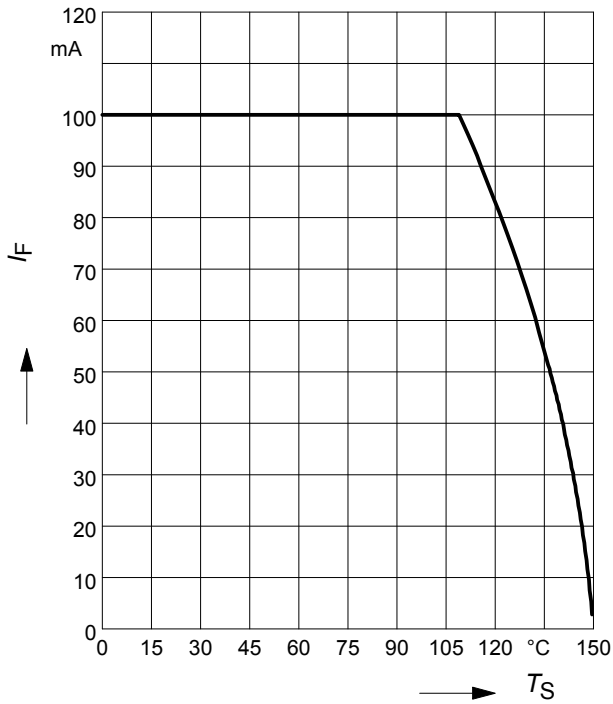
$T_A = \text{Parameter}$



Intermodulation intercept point
 $IP_3 = f(I_F); f = \text{Parameter}$

Forward current $I_F = f(T_S)$
BAR64-02EL

Forward current $I_F = f(T_S)$
BAR64-02V

Forward current $I_F = f(T_S)$
BAR64-04, BAR64-05, BAR64-06


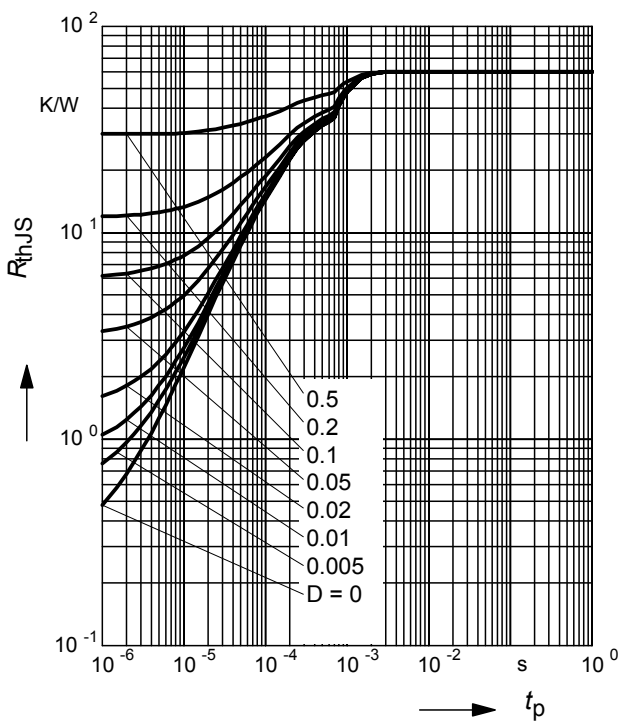
Forward current $I_F = f(T_S)$

BAR64-04W, BAR64-05W, BAR64-06W



Permissible Puls Load $R_{thJS} = f(t_p)$

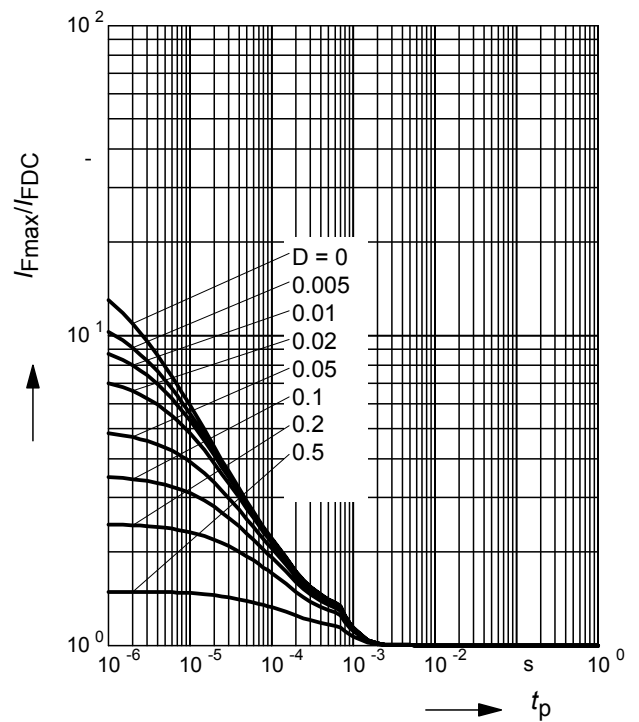
BAR64-02EL



Permissible Pulse Load

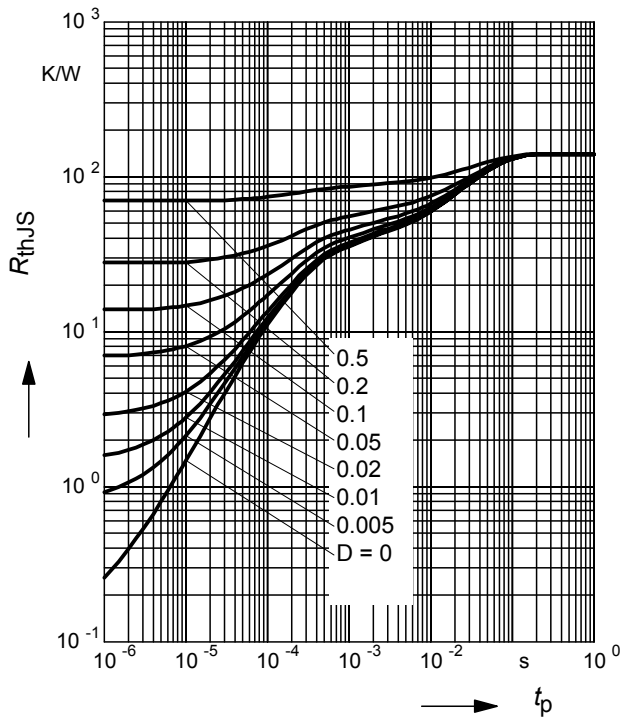
$I_{Fmax}/I_{FDC} = f(t_p)$

BAR64-02EL



Permissible Puls Load $R_{thJS} = f(t_p)$

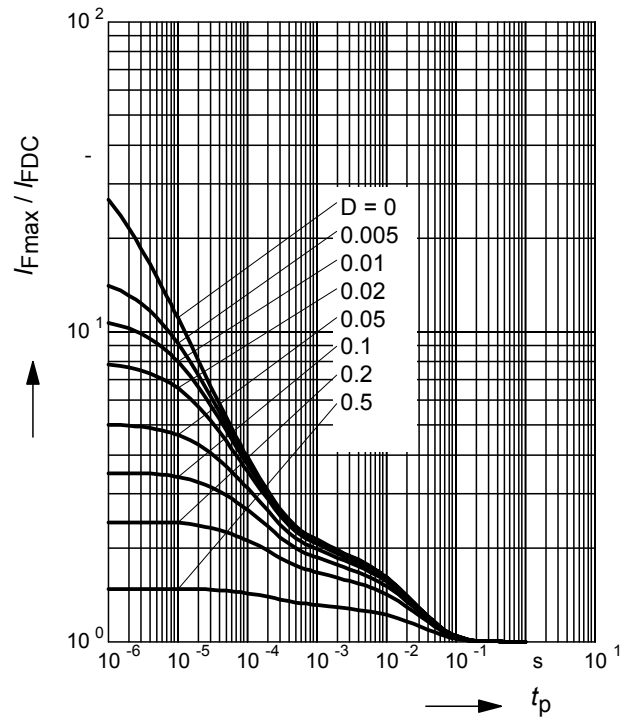
BAR64-02V



Permissible Pulse Load

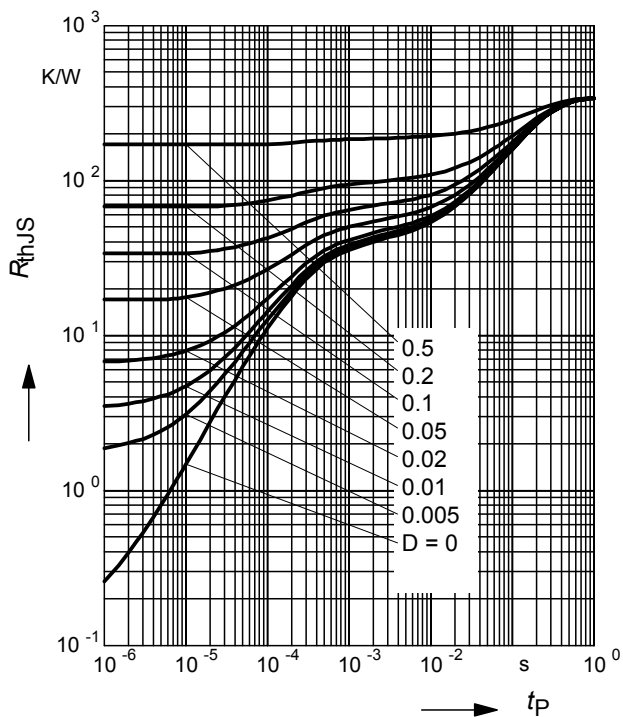
$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAR64-02V



Permissible Puls Load $R_{thJS} = f(t_p)$

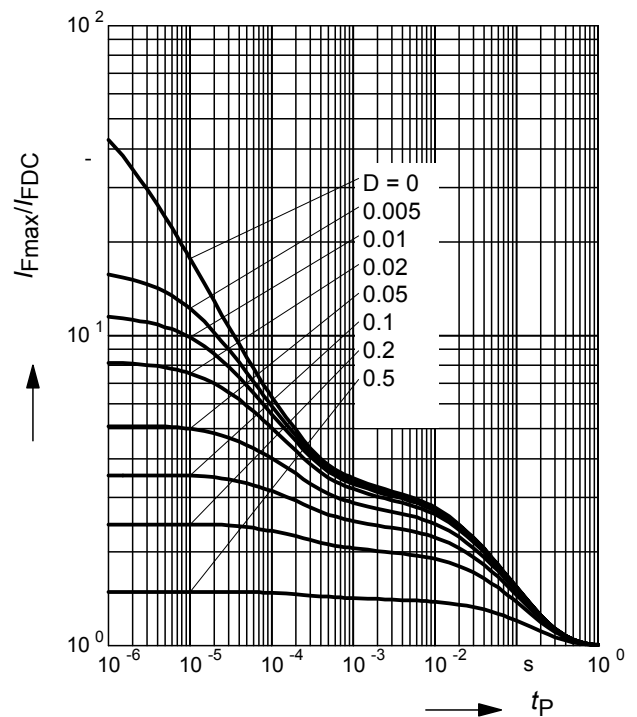
BAR64-04, BAR64-05, BAR64-06



Permissible Pulse Load

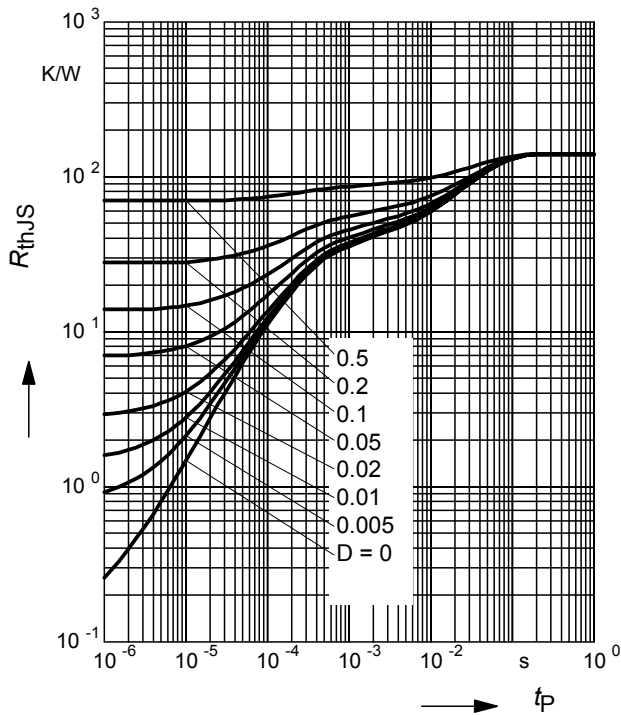
$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAR64-04, BAR64-05, BAR64-06



Permissible Puls Load $R_{thJS} = f(t_p)$

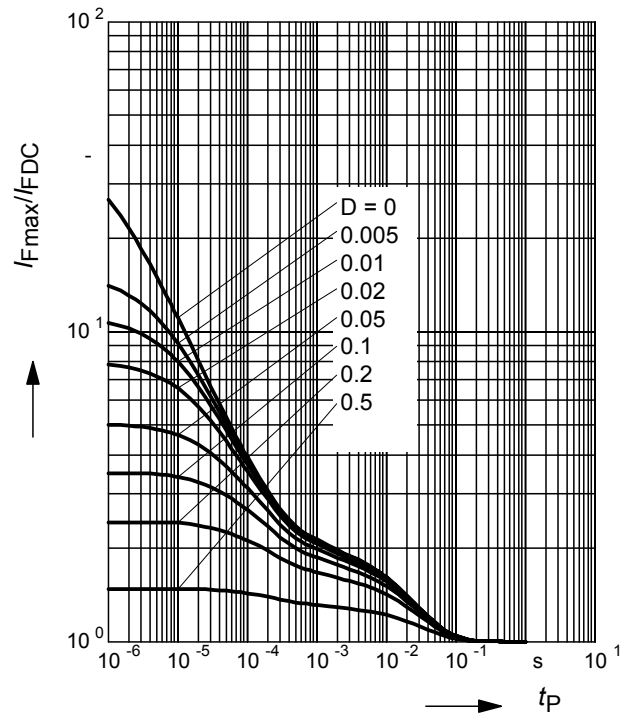
BAR64-04W, BAR64-05W, BAR64-06W



Permissible Pulse Load

$$I_{Fmax}/I_{FDC} = f(t_p)$$

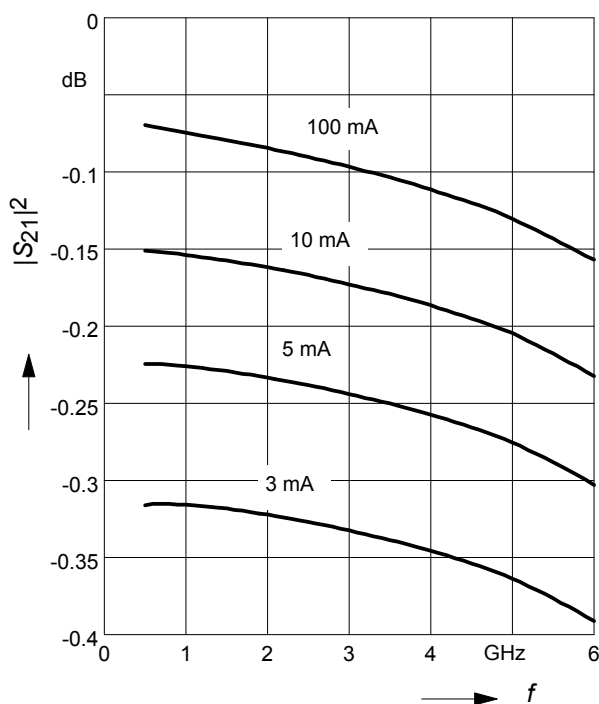
BAR64-04W, BAR64-05W, BAR64-06W



Insertion loss $I_L = -|S_{21}|^2 = f(f)$

I_F = Parameter

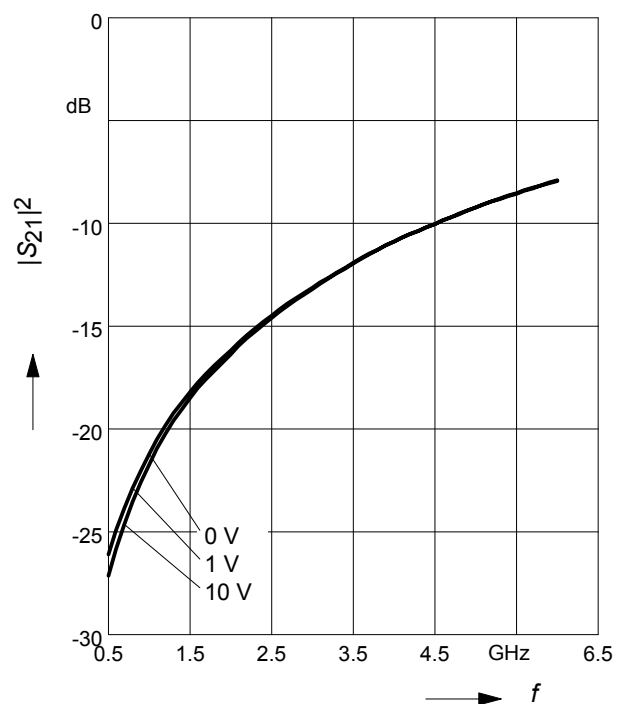
BAR64-02EL in series configuration, $Z = 50\Omega$



Isolation $I_{SO} = -|S_{21}|^2 = f(f)$

V_R = Parameter

BAR64-02EL in series configuration, $Z = 50\Omega$



[illegible]

2005, June
Date code

BAR63-02V
Type code

Cathode marking
Laser marking

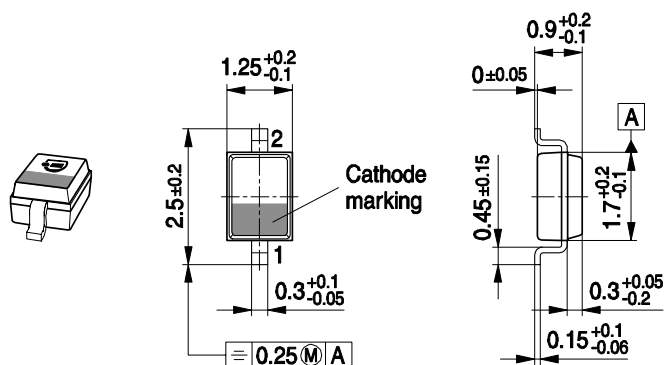
The image contains three technical drawings of cathode marking components. The first drawing, labeled 'Standard', shows a component with a width of 4, a height of 8, and a pitch of 1.33. It features two circular cathode markings and two rectangular markings. The second drawing, labeled 'Reel with 2 mm Pitch', shows a component with a width of 2, a height of 0.66, and a pitch of 1.96. It features two circular cathode markings and two rectangular markings. The third drawing shows a side view of the component with a width of 0.2 and a height of 0.66. Arrows indicate the direction of the cathode marking.

Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

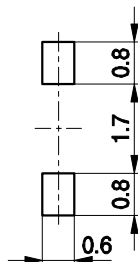
Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

1) New Marking Layout for SC75, implemented at October 2005.

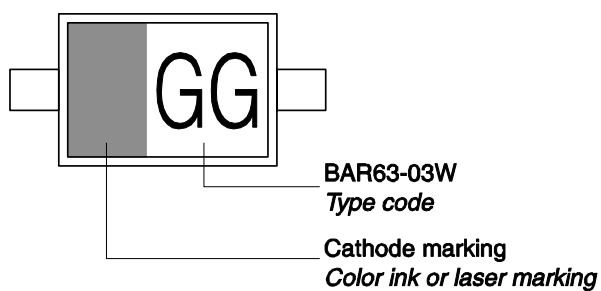
Package Outline



Foot Print

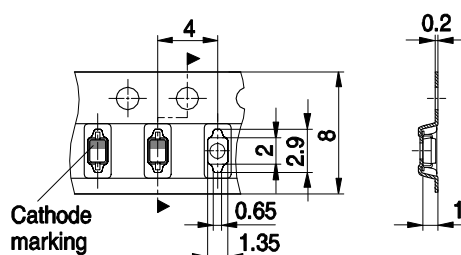


Marking Layout (Example)

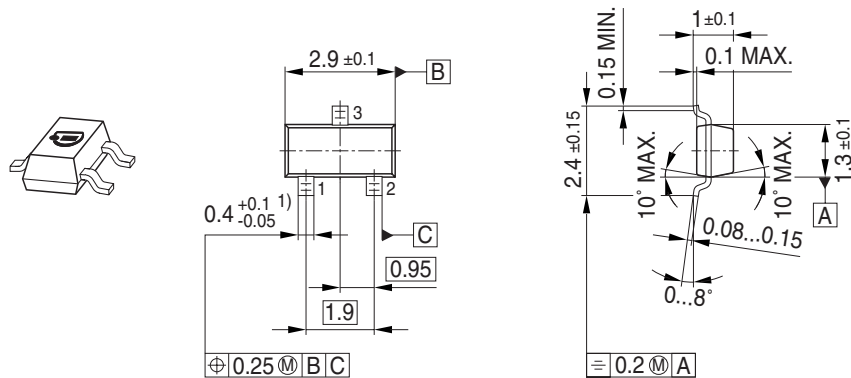


Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel

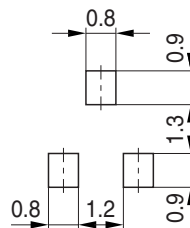


Package Outline

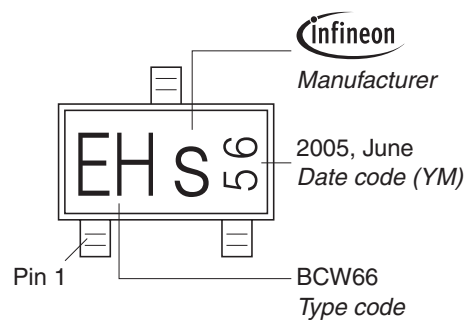


1) Lead width can be 0.6 max. in dambar area

Foot Print

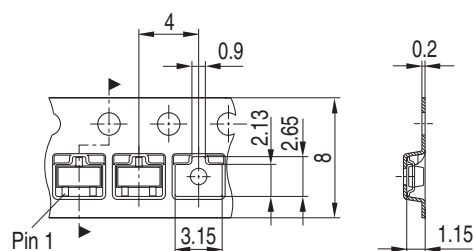


Marking Layout (Example)

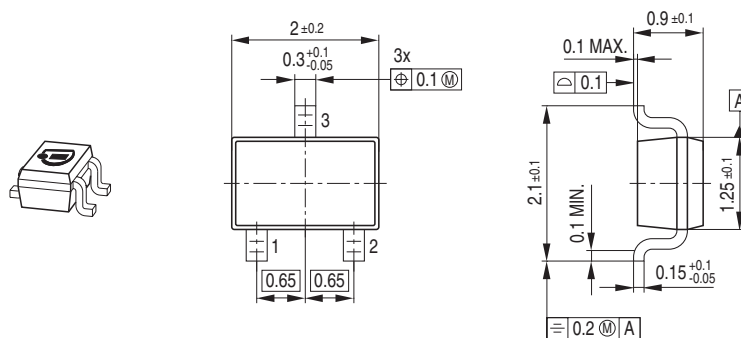


Standard Packing

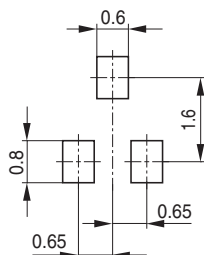
Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel



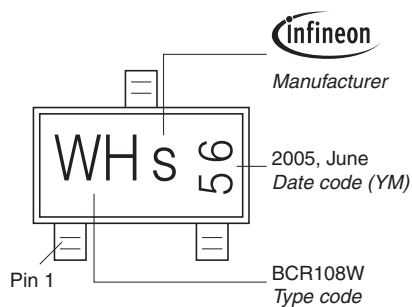
Package Outline



Foot Print

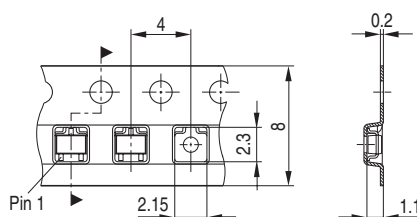


Marking Layout (Example)

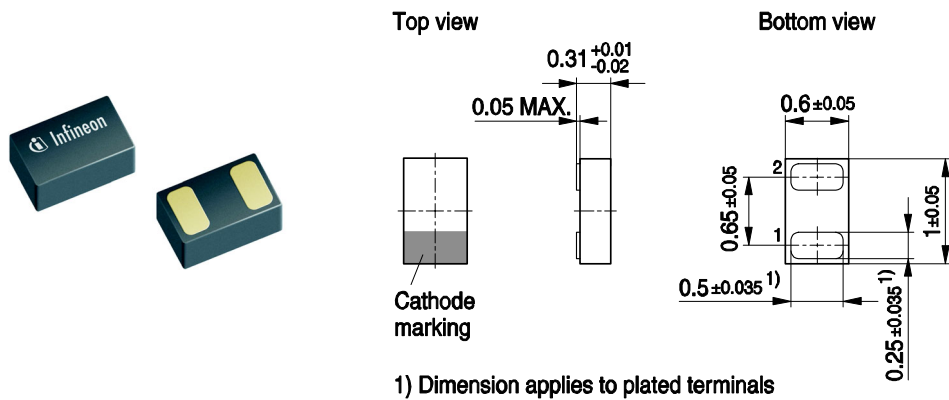


Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel



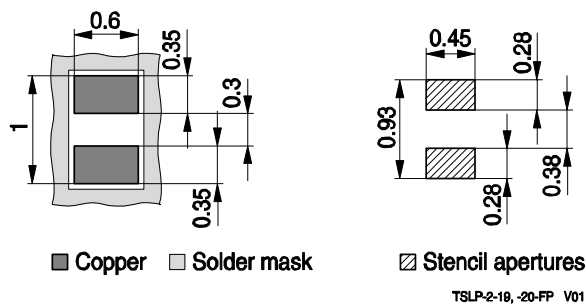
Package Outline



TSLP-2-19, -20-PO V01

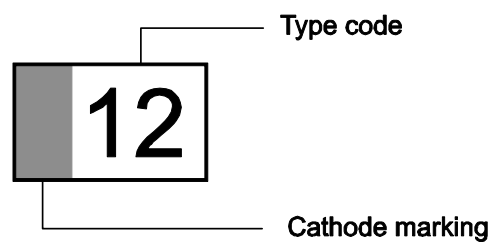
Foot Print

For board assembly information please refer to Infineon website „Packages“



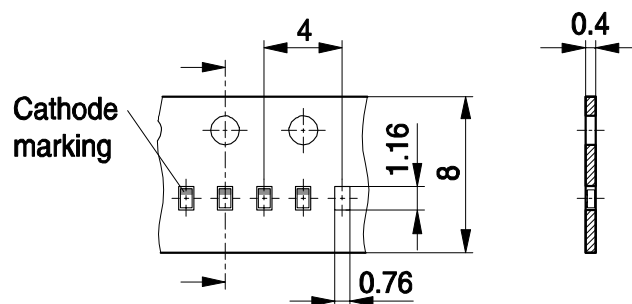
TSLP-2-19, -20-FP V01

Marking layout (Example)



Standard Packing

Reel Ø 180 mm: 15.000 Pieces / Reel
 Reel Ø 330 mm: 6.000 Pieces / Reel
 Reel Ø 330 mm: 50.000 Pieces / Reel



TSLP-2-19, -20-TP V02

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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